

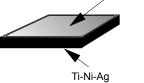
Data Sheet

Features

MI Т ΕD

Oxide Passivated Junction Very Low Forward Voltage 125 ° C Junction Operating Low Reverse Leakage Supplied as Wafers Chromium Barrier >1000V ESD (MM)

Cr-Al-Ni-Ag - Suffix "Ag"





Electrical Characteristics @ 25°c	Symbol	Unit	SB051C025-1-W-Ag (See ordering code below)
Maximum Repetitive Reverse Voltage (2)	V _{RRM}	Volt	25
Maximum Forward Voltage @ I_F = 1A (1)(2)	V _F	Volt	0.33
Typical Average Forward Rectified Current (2)	I _{F(AV)}	Amp	1
Reverse Leakage Current @ V_R = 25V (2)	I _{R(1)}	μA	600
Reverse Leakage Current @ V_R = 25V, 125°C (2)	I _{R(2)}	mA	50
ESD Machine Model (MM)	V _{ESD(mm)}	Volt	>1000
Junction Operating Temperature Range (2)	TJ	°C	-45 to +125
Storage Temperature Range (2)	T _{SG}	°C	-45 to +125

(1) Pulse Width tp = $< 300\mu$ S, Duty Cycle < 2%

(2) The characteristics above assume the die are assembled in industry standard packages using appropriate attach methods.

